

**Silicon PNP Power Transistors**

**2SA882**

**DESCRIPTION**

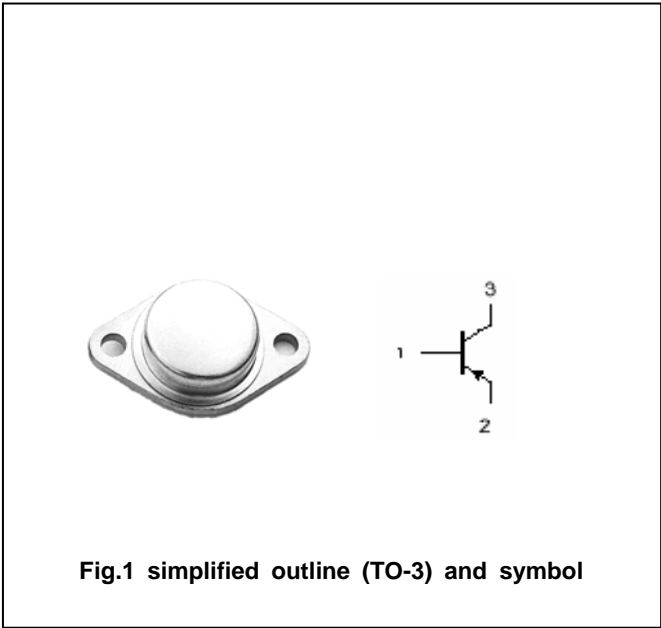
- With TO-3 package
- Excellent Safe Operating Area

**APPLICATIONS**

- For power and switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Fig.1 simplified outline (TO-3) and symbol**

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-130	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-130	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-7	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	1.52	°C/W

## Silicon PNP Power Transistors

## 2SA882

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-30mA ; I <sub>B</sub> =0	-130			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-7A ; I <sub>B</sub> =-1.5A			-3.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V			-1.6	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CE</sub> =-130V; I <sub>B</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V	40			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V	20			

PACKAGE OUTLINE

